

Abstract: (Fig. 6)

"SEMICONDUCTOR DEVICE"

In the crystal structure of a polysilicon thin film (3) having a field effect mobility μ_{FE} of about 80 cm²/V·sec, the grain size is about 200 nm and the crystallite size on the (111) plane is about 180 nm.

5 The crystallite size corresponds to the size of a completely monocrystallized portion of a grain. The condition of obtaining a field effect mobility μ_{FE} of about 80 cm²/V·sec is that the crystallite size on the (111) plane is at least 180 nm (measured value). By taking

10 the crystal size into consideration, it becomes possible to achieve a high field effect mobility μ_{FE} which cannot be obtained merely by increasing the grain size.

This Sheet Has Been Replaced

